

# J107, J108 J109, J110

CASE 29-02, STYLE 5  
TO-92 (TO-226AA)

JFET  
GENERAL-PURPOSE  
TRANSISTOR

N-CHANNEL — DEPLETION

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Gate Voltage	V <sub>DG</sub>	-25	Vdc
Gate-Source Voltage	V <sub>GS</sub>	-25	Vdc
Gate Current	I <sub>G</sub>	10	mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	310 2.82	mW mW/°C
Junction Temperature Range	T <sub>J</sub>	135	°C
Storage Channel Temperature Range	T <sub>stg</sub>	-65 to +150	°C

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Gate-Source Breakdown Voltage (V <sub>DS</sub> = 0, I <sub>G</sub> = -10 μAdc)	V <sub>(BR)GSS</sub>	-25	—	—	Vdc
Gate Reverse Current (V <sub>GS</sub> = -15 Vdc, V <sub>DS</sub> = 0) (V <sub>GS</sub> = -15 Vdc, V <sub>DS</sub> = 0, T <sub>A</sub> = 100°C)	I <sub>GSS</sub>	—	—	-3.0 -200	nAdc
Gate Source Cutoff Voltage (V <sub>DS</sub> = 15 Vdc, I <sub>D</sub> = 10 nAdc)	V <sub>GS(off)</sub>	J107 -0.5 J108 -3.0 J109 -2.0 J110 -0.5	— — — —	-4.5 -10 -6.0 -4.0	Vdc

### ON CHARACTERISTICS

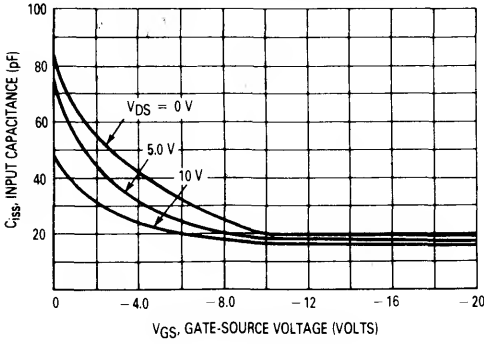
Zero-Gate-Voltage Drain Current(1) (V <sub>DS</sub> = 15, V <sub>GS</sub> = 0)	I <sub>DSS</sub>	J107 100 J108 80 J109 40 J110 10	— — — —	— — — —	mAdc
Drain-Source On-Resistance (V <sub>DS</sub> < 0.1 V, V <sub>GS</sub> = 0 V)	r <sub>DS(on)</sub>	J107 — J108 — J109 — J110 —	— — — —	8.0 8.0 12 18	ohms

### SMALL-SIGNAL CHARACTERISTICS

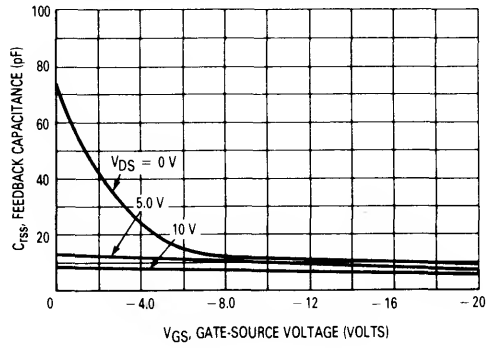
Drain Gate + Source Gate On-Capacitance (V <sub>DS</sub> = 0 Vdc, V <sub>GS</sub> = 0, f = 1.0 MHz)	C <sub>dg(on)</sub> + C <sub>sg(on)</sub>	—	—	85	pF
Drain Gate Off-Capacitance (V <sub>DS</sub> = 0 Vdc, V <sub>GS</sub> = -10 V, f = 1.0 MHz)	C <sub>dg(off)</sub>	—	—	15	pF
Source Gate Off-Capacitance (V <sub>DS</sub> = 0 Vdc, V <sub>GS</sub> = -10 V, f = 1.0 MHz)	C <sub>sg(off)</sub>	—	—	15	pF

(1) Pulse Duration 300 μs, Duty Cycle ≤ 2.0%.

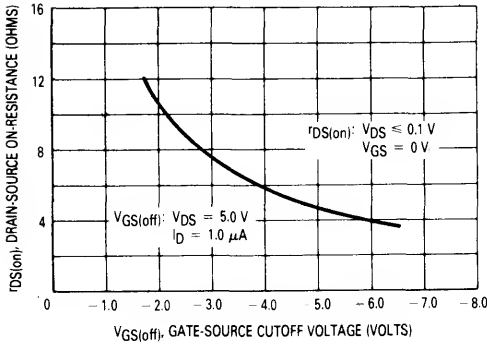
**FIGURE 1 — COMMON SOURCE INPUT CAPACITANCE versus GATE-SOURCE VOLTAGE**



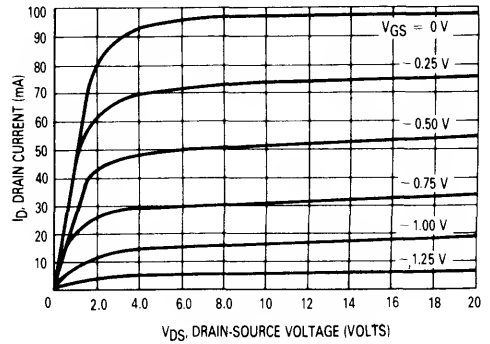
**FIGURE 2 — COMMON SOURCE REVERSE FEEDBACK CAPACITANCE versus GATE-SOURCE VOLTAGE**



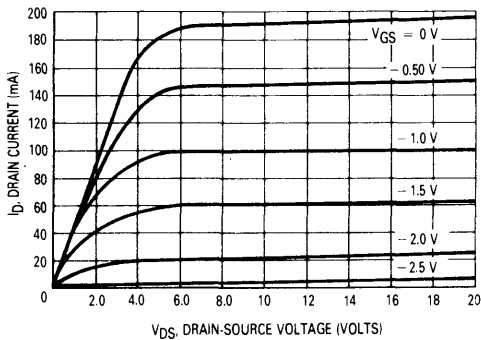
**FIGURE 3 — ON-RESISTANCE versus GATE-SOURCE CUTOFF VOLTAGE**



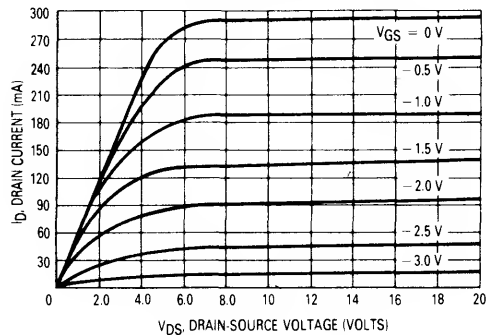
**FIGURE 4 — OUTPUT CHARACTERISTIC**  
 $V_{GS(off)} = -2.0 \text{ V}$



**FIGURE 5 — OUTPUT CHARACTERISTIC**  
 $V_{GS(off)} = -3.0 \text{ V}$



**FIGURE 6 — OUTPUT CHARACTERISTIC**  
 $V_{GS(off)} = -4.0 \text{ V}$



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FIGURE 7 — OUTPUT CHARACTERISTIC

$V_{GS(off)} = -5.0\text{ V}$

